

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

2SK711

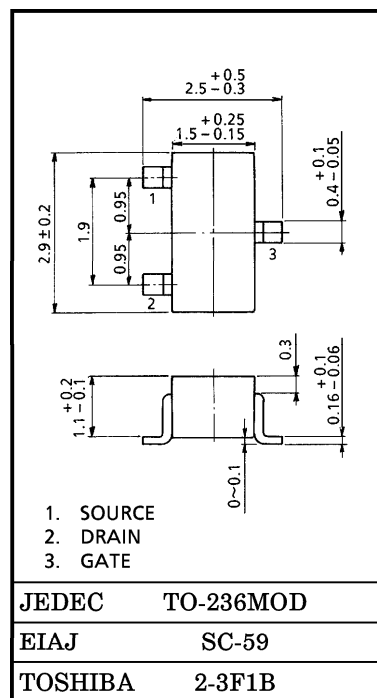
HIGH FREQUENCY AMPLIFIER APPLICATIONS
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 AUDIO FREQUENCY AMPLIFIER APPLICATIONS

Unit in mm

- High $|Y_{fs}|$: $|Y_{fs}|=25\text{mS}$ (Typ.)
- Low C_{iss} : $C_{iss}=7.5\text{pF}$ (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	-20	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	150	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

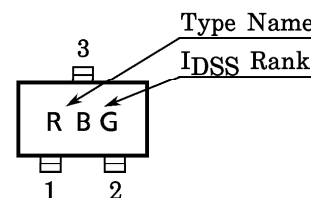
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS} = -15V, V_{DS} = 0V$	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS} = 0V, I_G = -100\mu A$	-20	—	—	V
Drain Current	I_{DSS} (Note)	$V_{DS} = 5V, V_{GS} = 0V$	6	—	32	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 5V, I_D = 1\mu A$	—	—	-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 5V, V_{GS} = 0V, f = 1\text{kHz}$	15	25	—	mS
Input Capacitance	C_{iss}	$V_{DS} = 5V, V_{GS} = 0V, f = 1\text{MHz}$	—	7.5	10	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 5V, I_D = 0\text{mA}, f = 1\text{MHz}$	—	2	3	pF

Marking

Note: I_{DSS} Classification

GR : 6~12mA, BL : 10~20mA, V : 16~32mA
 (G) (L) (V)

() ... I_{DSS} Rank Markng



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